



| Crystal Properties | | | |
|---------------------------------------|-----------------------|-------------------|------|
| PARAMETER | UNITS | SPECIFICATION | NOTE |
| Crystalline structure | - | Monocrystalline | |
| Growth technique | - | Czochralski (Cz) | |
| Orientation | - | <100> ±1° | |
| Slice orientation | Degrees | ON ±1.0° | |
| Electrical Properties | | | |
| PARAMETER | UNITS | SPECIFICATION | NOTE |
| Conductance type | - | P-type | |
| Dopant | - | Boron | |
| Resistivity | Ω-cm | 5 - 30 | |
| Geometrical Properties | | | |
| PARAMETER | UNITS | SPECIFICATION | NOTE |
| Diameter | mm | 200±0.2 | |
| Thickness | μm | 725±25 | |
| TTV | μm | ≤4 | |
| Warp | μm | ≤40 | |
| Bow | μm | ≤60 | |
| Notch | - | SEMI standard | |
| Notch depth | mm | 1.0 + 0.25 – 0.00 | |
| Notch angle | - | 90° +5° -1° | |
| Notch orientation | - | <110> ±1° | |
| Surface Appearance | | | |
| PARAMETER | UNITS | SPECIFICATION | NOTE |
| Front surface | - | Polished | |
| Back surface | - | Etched | |
| Frontside particles ≥0.16 μm (LPD) | No./wafer | ≤50 | |
| Nominal edge exclusion | mm | 3.0 | |
| Wafer Identification | | | |
| PARAMETER | UNITS | SPECIFICATION | NOTE |
| Lasermark | - | None | |
| Surface Metals | | | |
| APPLICABLE METALS | UNITS | SPECIFICATION | NOTE |
| Al, Ca, Cl, Cr, Cu, Fe, K, Na, Ni, Zn | Atoms/cm ² | ≤5E10 | |